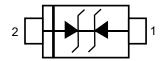


Description

The TVS5V6 SOD-323 ESD protector is designed to replace multilayer varistors (MLVs) in portable applications such as cell phones, notebook computers, and PDA's. They feature large cross-sectional area junctions for conducting high transient currents, offer desirable electrical characteristics for board level protection, such as fast response time, lower operating voltage, lower clamping voltage and no device degradation when compared to MLVs. The SXTVS3D5VC protects sensitive semiconductor components from damage or upset due to electrostatic discharge (ESD) and other voltage induced transient events. The SXTVS3D5VC is available in a SOD-323 package with working voltages of 5 volt. It is used to meet the ESD immunity requirements of IEC 61000-4-2, (±30kV air, ±30kV contact discharge)



Feature

- ≥ 2000W Peak pulse power per line (t_P = 8/20µs)
- SOD-323 package
- Response time is typically < 1 ns</p>
- Protect one I/O or power line
- Low clamping Voltage
- RoHS compliant
- Transient protection for data lines to IEC 61000-4-2(ESD) > ±30KV(air), ±30KV(contact); IEC 61000-4-4 (EFT) 40A (5/50ns)>

Applications

- Cell phone handsets and accessories
- Personal digital assistants (PDA's)
- Notebooks, desktops, and servers
- Portable instrumentation
- Cordless phones
- Digital cameras
 - Peripherals
 - MP3 players

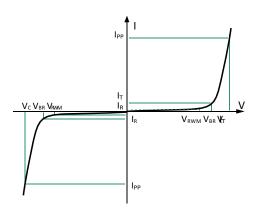
Mechanical Characteristics

- Lead finish:100% matte Sn(Tin)
- Mounting position: Any
- ➤ Qualified max reflow temperature:260 °C
- ➤ Pure tin plating: 7 ~ 17 um
- Pin flatness:≤3mil



Electronics Parameter

Symbol	Parameter		
V _{RWM}	Peak Reverse Working Voltage		
I _R	Reverse Leakage Current @ V _{RWM}		
V_{BR}	Breakdown Voltage @ I _⊺		
I _T	Test Current		
I _{PP}	Maximum Reverse Peak Pulse Current		
Vc	Clamping Voltage @ IPP		
P _{PP}	Peak Pulse Power		
CJ	Junction Capacitance		



Electrical characteristics per line@25 °C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Reverse Working Voltage ⁽¹⁾	V _{RWM}				5.0	V
Breakdown Voltage	V_{BR}	I _t =1mA	5.1			V
Reverse Leakage Current	I _R	V _{RWM} =5.0V			1	μA
Clamping Voltage(PIN2~PIN1)	Vc	I _{PP} =20A t _P = 8/20μs		6.5	8	V
Clamping Voltage(PIN2~PIN1)	Vc	I _{PP} =45A t _P = 8/20μs		7.5	9	V
Clamping Voltage(PIN2~PIN1)	Vc	I _{PP} =90A t _P = 8/20μs		9.5	12	V
Clamping Voltage(PIN2~PIN1)	Vc	I _{PP} =130A t _P = 8/20μs		11.5	15	V
Junction Capacitance	Cj	V _R =0V f = 1MHz		320	400	pF

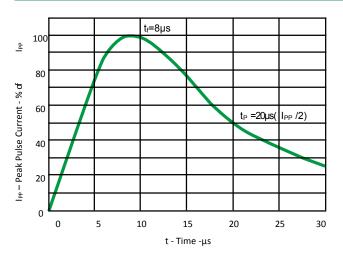
Note 1: V_{RWM} is the maximum reverse working voltage, or reverse stand-off voltage. ESD can protect signal line properly within its rated voltage. If the signal line's voltage is over V_{RWM} , ESD will change to other state.

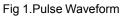
Absolute maximum rating@25℃

Rating	Symbol	Value	Units
Peak Pulse Power (t _P = 8/20μS)	P_{pp}	2000	W
Total Device Dissipation FR-5 Board	P _D	500	mW
Lead Soldering Temperature	T∟	260 (10 sec)	$^{\circ}$
Operating Temperature	TJ	-55 to +125	°C
Storage Temperature	T _{STG}	-55 to +150	°C



Typical Characteristics





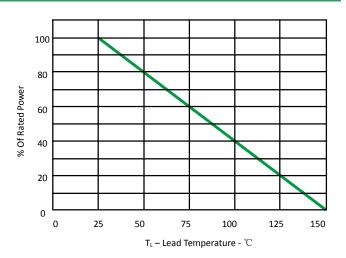


Fig 2.Power Derating Curve

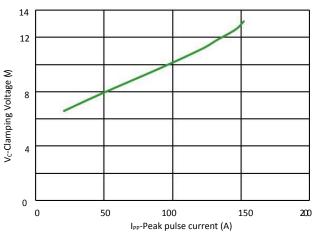


Fig 3. Clamping voltage vs. Peak pulse current

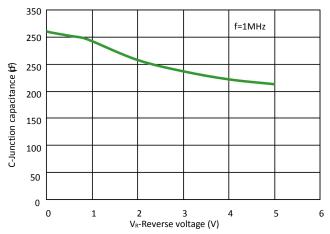


Fig 4. Capacitance vs. Reveres voltage

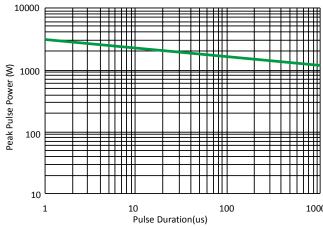
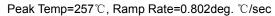
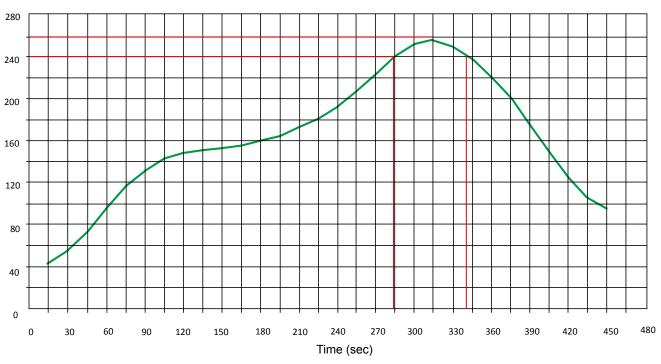


Fig 5. Non Repetitive Peak Pulse Power vs. Pulse time



Solder Reflow Recommendation





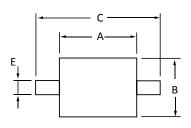
PCB Design

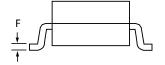
For TVS diodes a low-ohmic and low-inductive path to chassis earth is absolutely mandatory in order to achieve good **D** protection. Novices in the area of ESD protection should take following suggestions to heart:

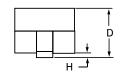
- Do not use stubs, but place the cathode of the TVS diode directly on the signal trace.
- Do not make false economies and save copper for the ground connection.
- Place via holes to ground as close as possible to the anode of the TVS diode.
- Use as many via holes as possible for the ground connection.
- > Keep the length of via holes in mind! The longer the more inductance they will have.



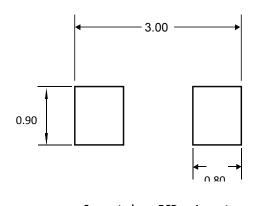
Product dimension (SOD-323)







Dim	Incl	nes	Millimeters		
	MIN	MAX	MIN	MAX	
Α	0.063	0.075	1.60	1.90	
В	0.045	0.057	1.15	1.45	
С	0.090	0.106	2.30	2.70	
D	0.031	0.043	0.80	1.00	
E	0.010	0.01	0.25	0.40	
F	0.004	0.007	0.09	0.18	
Н	0.000	0.004	0.00	0.10	



Suggested PCB Layout

Unit:mm